

[from the remainder of] within said semiconductor material; and ^{what is extending vertically?}
[said layer] extending vertically from said surface regions, [beginning at a level] and having an upper boundary more shallow than the depth of said dielectric isolation zone, and [extending to] a lower boundary having a depth greater than the depth of said [dielectric] isolation zone, said isolation zone having a depth of 300 to 400 nm.

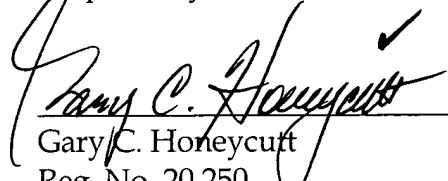
↳ not necessarily the same as "the depth"

REMARKS

Favorable reconsideration and allowance of the application are respectfully requested in view of the above amendments and the following comments.

The substance of claim 8, conditionally allowable, has now been added to claim 1.
Claims 1 - 7 should now be allowable.

Respectfully submitted,



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